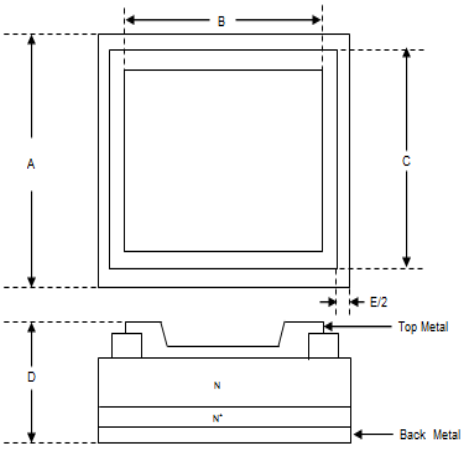
TSB94S150S(A)S-255A

10A/150V(1), low VF Schottky barrier diode with trench MOS structure

Mechanical Data

Chip Drawing	Item	Information	
	Die Size (A)	2388 μm	94 mil
	Top Metal Pad Size (B)	2286μm	90mil
	Chip Size (C)	2311μm	91mil
	Wafer Thickness (D)	255 μm	9.5 mil
	Scribe Line Width (E)	80 μm	3.15 mil
	Wafer Size	6 inch	
	Top Side Metallization	AL/Ag	
	Back Side Metallization	Ti Ni Ag	
	Recommended Storage Environment	Stored in original container, in dry nitrogen, (6 months at an ambient temperature of 23 ±3)	

Electrical Characteristics (T_J=25℃, unless otherwise specified)(2)

Parameter	Description	Min.	Typ.	Max.	Unit	Test Condition
V_{BR}	Reverse Breakdown Voltage	155	170	-	V	I_R =100μA
V_F	Instantaneous Forward Voltage	-	0.8	0.88	V	I_F =10A(3)
I_R	Reverse Leakage Current	-	0.5	10		V_R =150V
T_J, T_{STG}	Operating and Storage Temperature	-40	to 150	Max		